



NDF08N60ZH Information



For Reference Only

Part Number NDF08N60ZH
Manufacturer ON Semiconductor

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 600V 8.4A TO-220FP

Package TO-220-3 Full Pack

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









NDF08N60ZH Specifications

Manufacturer Part Number NDF08N60ZH Manufacturer ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-220-3 Full Pack Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 8.4A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 4.5V @ 100µA Gate Charge (Qg) (Max) @ Vgs 58nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1370pF @ 25V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 36W (Tc) Rds On (Max) @ Id, Vgs 950 mOhm @ 3.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack		
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TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C8.4A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 100μAGate Charge (Qg) (Max) @ Vgs58nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1370pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)36W (Tc)Rds On (Max) @ Id, Vgs950 mOhm @ 3.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220FPPackage / CaseTO-220-3 Full Pack	Series	-
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Current - Continuous Drain (Id) @ 25°C B.4A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature John Charge (Ciss) (Max) @ Vds Through Hole Supplier Device Package Package / Case 8.4A (Tc) 8.4C (100 μ) 8.4C (100 μ	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4.5V @ 100μAGate Charge (Qg) (Max) @ Vgs58nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1370pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)36W (Tc)Rds On (Max) @ Id, Vgs950 mOhm @ 3.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220FPPackage / CaseTO-220-3 Full Pack	Drain to Source Voltage (Vdss)	600V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1370pF @ 25V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-220-3 Full Pack	Current - Continuous Drain (Id) @ 25°C	8.4A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 1370pF @ 25V Vgs (Max) ±30V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 950 mOhm @ 3.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Through Hole Supplier Device Package TO-220FP Package / Case 1370pF @ 25V	Vgs(th) (Max) @ Id	4.5V @ 100μA
Vgs (Max)±30VFET Feature-Power Dissipation (Max)36W (Tc)Rds On (Max) @ Id, Vgs950 mOhm @ 3.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220FPPackage / CaseTO-220-3 Full Pack	Gate Charge (Qg) (Max) @ Vgs	58nC @ 10V
FET Feature - Power Dissipation (Max) 36W (Tc) Rds On (Max) @ Id, Vgs 950 mOhm @ 3.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	Input Capacitance (Ciss) (Max) @ Vds	1370pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 950 mOhm @ 3.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs950 mOhm @ 3.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220FPPackage / CaseTO-220-3 Full Pack	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	Power Dissipation (Max)	36W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	Rds On (Max) @ Id, Vgs	950 mOhm @ 3.5A, 10V
Supplier Device Package TO-220FP Package / Case TO-220-3 Full Pack	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3 Full Pack	Mounting Type	Through Hole
	Supplier Device Package	TO-220FP
Report errors?	Package / Case	TO-220-3 Full Pack
		Report errors?

NDF08N60ZH Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

NDF08N60ZH Payment Methods





















NDF08N60ZH Shipping Methods













If you have any question about NDF08N60ZH, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com